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2nd mixer and IF amplifier IC for digital cellular BH4138FV

The BH4138FV is an IC developed for use with digital cellular phones. This IC contains a 2nd mixer and IF amplifier.

Applications

Digital cellular phones

Features

- Mixer circuit, IF amplifier, and RSSI circuit are builtin.
- 2) Mixer input frequency response 10MHz to 200MHz.
- The recommended IF amplifier frequencies are 450kHz and 455kHz.
- 4) High gain IF amplifier (100dB).
- 5) Battery saving function.
- 6) Buffer amplifier for RSSI.
- 7) Low voltage operation (2.3V to 5.5V).

● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Power supply voltage	Vcc	7.0	V
Power dissipation	Pd	350 ^{*1}	mW
Storage temperature	Tsig	−55∼ +125	င

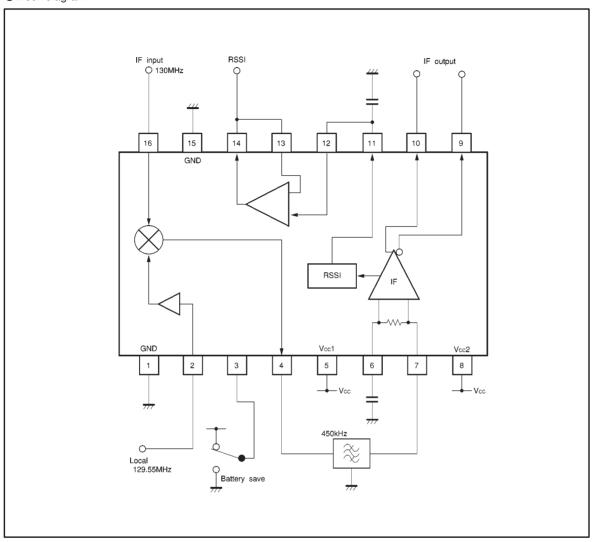
^{*1} Reduced by 3.5mW for each increase in Ta of 1 $^{\circ}$ C over 25 $^{\circ}$ C.

• Recommended operating conditions (Ta = 25°C)

Parameter	Symbol	Limits	Unit	Conditions
Operating power supply voltage	Vcc	2.3~5.5	V	_
Operating temperature	Topr	−40~ +85	°C	_
Mixer input frequency	fmix in	10~200	MHz	pin 16
Mixer output frequency	fміх out	350~500	kHz	pin 4
IF input frequency	fiF IN	350~500	kHz	pin 7
Mixer input level	V _{MIX} IN	10~95	dB μV	pin 16
Local input level	V LO IN	95~105	dB μV	pin 2
IF input level	VIF IN	15~100	dB μV	pin 7
Battery saving input voltage	V тн-н	2~Vcc	V	Active
	V _{TH-L}	-0.3~+0.2	V	Battery saving



■Block diagram



Pin descriptions

Pin No.	Function	Equivalent circuit	DC voltage (V)
1	GND	GND	GND
2	Local oscillation input pin Input from the external oscillator.	2 to MIXER 15p White to Mixe	
3	Battery saving pin Vp3≦ 0.2V : battery saving 2V ≦ Vp3 ≦ Vcc : active (Vp3 : voltage at pin 3)	3 50k VVV	
4	Mixer output pin Connect to ceramic filter. Output impedance is $2k\Omega$	1.9k	Vcc-1.6
5	Power supply pin	The power supply for mixer stage and front of the IF amplifier.	Vcc

Pin No.	Function	Equivalent circuit	DC voltage (V)
6	IF amplifier output pin Connect a capacitor.	Vcc 15k \$ 1k \\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	Vcc-0.6
7	IF amplifier input pin Connect a ceramic filter. Input impedance is $2k\Omega$		Vcc-0.6
8	Power supply pin 2	The power supply for the IF rear stage.	Vcc
9,10	IF amplifier output pin Pins 9 and 10 output opposite phase.	9 Vcc Vcc Vcc Vcc Vcc Vcc Vcc Vcc Vcc Vc	Vcc-1.2
11	RSSI output pin Connect a capacitor.	11 Vcc	0.15

Pin No.	Function	Equivalent circuit	DC voltage (V)
12	Non-inverting input pin of the buffer amplifier	V _{cc}	
13	Inverting input pin of the buffer amplifier		
14	Output pin of the buffer amplifier	200 W	
15	GND	GND	GND
16	Mixer input pin Input 1st IF signal by DC cut.	16 Voc	1.2

 $\begin{tabular}{ll} \blacksquare Electrical characteristics & (unless otherwise noted, Ta = 25 °C, Vcc = 3.0V, SG1 f_{IN(MIX)} = 130MHz, \\ SG2 f_{IN(LO)} = 129.55MHz, 100dB\mu V, SG3 f_{IN(IF)} = 450kHz) \\ \end{tabular}$

Alternating level to be indicated by termination.

*Items marked with an asterisk are reference values

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Quiescent current	lo	_	3.0	3.9	mA	V _{IN(LO)} =100dB μ V SW1=1
Quiescent current during battery saving	lo(BS)	_	0	5	μΑ	V _{IN(LO)} =100dB μV SW1=2
⟨MIX−local oscillator stage⟩			I			
Mixer conversion gain	Gvc	8.5	12.5	16.5	dB	V _{IN(MIX)} =60dB μ V SW2=1 (R _L =2kΩ)
1dB gain compression level*	Vом	96	101	_	dB μV	_
3rd order intercept point*	IРз	110	115	_	dB μV	f ₁ =130.05MHz, f ₂ =130.10MHz
Noise figure*	NF	_	8.5	12.5	dB	Matched impedance input
Mixer input admittance*	YIN(MIX)	0.38+j2.75		ms	f=130MHz G+jB	
Mixer output resistance*	R o(міх)	1.6	2	2.4	kΩ	_
Local oscillator input admittance*	YIN(LO)	С).25+j3.6	5	ms	f=130MHz G+jB
⟨IF stage⟩						
IF gain*	Gv	95	100	105	dB	_
Input resistance*	Rin(IF)	1.6	2	2.4	kΩ	_
Output level	Voif	0.7	1	1.3	V _{P-P}	V _{IN(IF)} =80dB μ V SW2=2
Output duty ratio	DR	45	50	55	%	V _{IN(IF)} =80dB μV, CL=10pF SW2=2
Phase delay*	ΔΦ	_	3	15	deg	$V_{IN(IF)}$ =30dB μ V \sim 105dB μ V

• Electrical characteristics (unless otherwise noted, Ta = 25 °C, Vcc = 3.0V, SG1 $f_{IN(MIX)}$ = 130MHz, SG2 $f_{IN(LO)}$ = 129.55MHz, 100dB μ V, SG3 $f_{IN(IF)}$ = 450kHz)

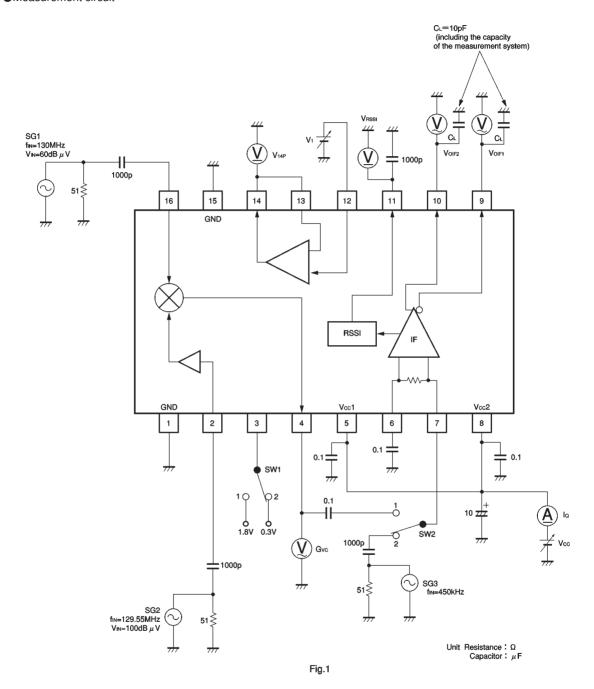
Alternating level to be indicated by termination.

*Items marked with an asterisk are reference values

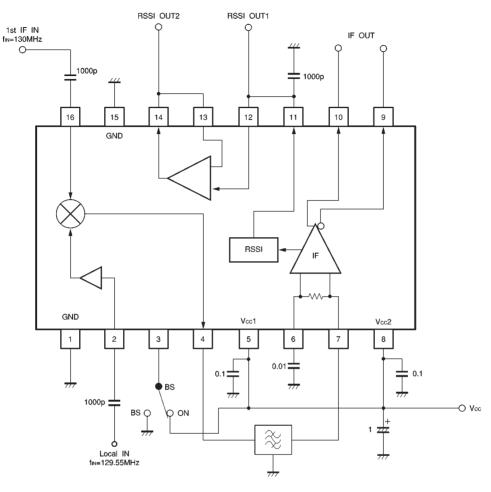
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
⟨RSSI stage⟩						
Output voltage 1	VRSSI1	_	0.15	0.4	V	No input SW2=2
Output voltage 2	VRSSI2	1.0	1.2	1.4	٧	V _{IN(IF)} =65dB μ V SW2=2
Output voltage 3	VRSSI3	1.9	2.0	2.2	V	V _{IN(IF)} =100dB μ V SW2=2
Output voltage 4	VRSSI4	0.5	0.7	0.9	V	V _{IN(IF)} =40dB μV SW2=2
Output voltage 5	VRSS15	1.4	1.6	1.8	v	V _{IN(IF)} =80dB μV SW2=2
Dynamic range*	Dr	80	85	_	dB	_
Linearity*	LR	_	_	±2.5	dB	It computes in the regression from VIN (MIX)=10dB μ V to 90dB μ V
Slope*	SR	1.91	21.3	23.4	mV/dB	It computes in the regression from V _{IN (MIX)} =10dB μ V to 90dB μ V
Output resistance*	Ro(rssi)	40	50	60	kΩ	_
Power supply ON rise time*	Ton	_	270	405	μs	C _L =100pF SW ₁ =2→1 V _{IN (MIX)} =35~100dB μV
Power supply OFF fall time*	Toff	_	130	195	μs	C _L =1000pF SW ₁ =1→2 V _{IN (MIX)} =35~100dB μV
RSSI rise time*	Tr	_	150	225	μs	CL=1000pF SG1=OFF \rightarrow VIN(MIX) VIN (MIX)=35 \sim 100dB μ V
RSSI fall time*	TF	-	410	615	μs	C _L =1000pF SG1=V _{IN(MIX)} →OFF V _{IN (MIX)} =35~100dB μV

ONot designed for radiation resistance.

Measurement circuit



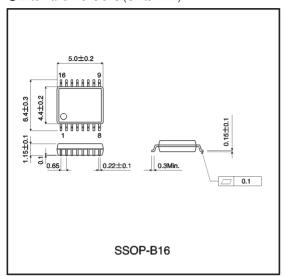
Application example



Unit Resistance : Ω Capacitor : μ F

Fig.2

●External dimensions (Units: mm)



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